

time such as ESD, but also a relatively long time of the millisecond order, can be improved.

FIG. 6 illustrates the high heat conductor layer 6 united with one of the terminal wirings 4A.

Please delete the Abstract of the Disclosure and insert the new Abstract of the Disclosure, attached.

IN THE CLAIMS:

Please cancel claim 1.

Please add the following new claim.

--6. A semiconductor device, comprising:
a semiconductor substrate;
a first insulating film formed on said semiconductor substrate;
a polysilicon resistor film formed on said first insulating film;
a second insulating film formed on said resistor film;
a high heat conductor film consisting of a highly heat-conducting material formed on
said second insulating film; and
a pair of terminal wirings formed on said second insulating film and connected to
said resistor film,
wherein a thickness of said second insulating film is thinner than a thickness of said
resistor film, and a thickness of said high heat conductor film is thicker than a thickness of
said resistor film.